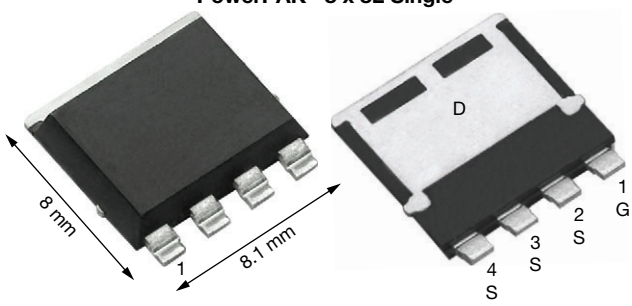
Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PowerPAK® 8 x 8L Single



Top View | Bottom View

FEATURES

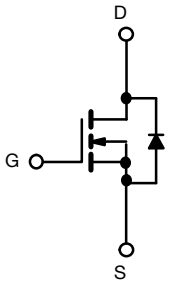
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

AUTOMOTIVE GRADE

Pb-free

RoHS COMPLIANT

HALOGEN FREE



N-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω) at V_{GS} = 10 V	0.0019
I_D (A)	200
Configuration	Single
Package	PowerPAK 8 x 8L

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	60	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current	T_C = 25 °C [a]	I_D	200	A
	T_C = 125 °C		118	
Continuous source current (diode conduction)		I_S	200	
Pulsed drain current [b]		I_{DM}	500	
Single pulse avalanche current	L = 0.1 mH	I_{AS}	75	
Single pulse avalanche energy		E_{AS}	281	mJ
Maximum power dissipation	T_C = 25 °C	P_D	150	W
	T_C = 125 °C		50	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature) [d, e]			260	

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount [c]	R_{thJA}	50	°C/W
Junction-to-case (drain)		R_{thJC}	1	

Notes

a. Package limited.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
c. When mounted on 1" square PCB (FR4 material).
d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8 x 8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

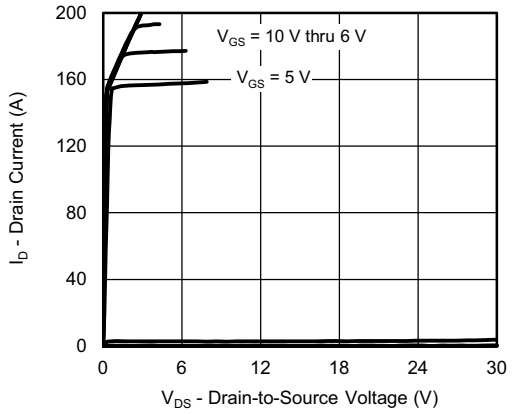
SPECIFICATIONS (T_C = 25 °C, unless otherwise noted)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static							
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0, I_D = 250 µA		60	-	-	V
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA		2.5	3	3.5	
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V		-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{GS} = 0 V	V_{DS} = 60 V	-	-	1	µA
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 125 °C	-	-	50	
		V_{GS} = 0 V	V_{DS} = 60 V, T_J = 175 °C	-	-	150	
On-state drain current [a]	$I_{D(on)}$	V_{GS} = 10 V	V_{DS} ≥ 5 V	100	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 10 A	-	0.0017	0.0019	Ω
		V_{GS} = 10 V	I_D = 10 A, T_J = 125 °C	-	-	0.0030	
		V_{GS} = 10 V	I_D = 10 A, T_J = 175 °C	-	-	0.0035	
Forward transconductance [b]	g_{fs}	V_{DS} = 15 V, I_D = 20 A		-	140	-	S
Dynamic [b]							
Input capacitance	C_{iss}	V_{GS} = 0 V	V_{DS} = 25 V, f = 1 MHz	-	8170	10 210	pF
Output capacitance	C_{oss}			-	3756	4700	
Reverse transfer capacitance	C_{rss}			-	70	88	
Total gate charge [c]	Q_g	V_{GS} = 10 V	V_{DS} = 30 V, I_D = 10 A	-	135	180	nC
Gate-source charge [c]	Q_{gs}			-	47	-	
Gate-drain charge [c]	Q_{gd}			-	14	-	
Gate resistance	R_g	f = 1 MHz		0.5	0.9	1.5	Ω
Turn-on delay time [c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 3 Ω I_D ≅ 10 A, V_{GEN} = 10 V, R_g = 1 Ω		-	24	30	ns
Rise time [c]	t_r			-	8	10	
Turn-off delay time [c]	$t_{d(off)}$			-	47	58	
Fall time [c]	t_f			-	15	19	
Source-Drain Diode Ratings and Characteristics [b]							
Pulsed current [a]	I_{SM}			-	-	300	A
Forward voltage	V_{SD}	I_F = 50 A, V_{GS} = 0		-	0.82	1.2	V

Notes

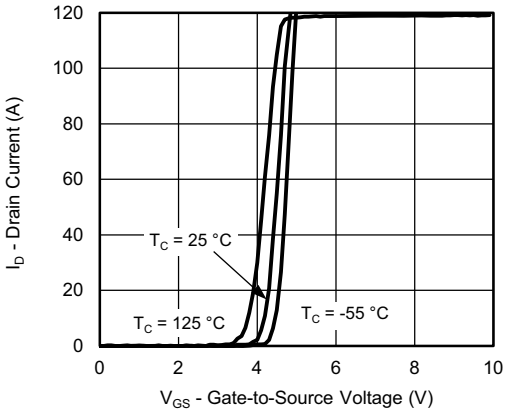
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

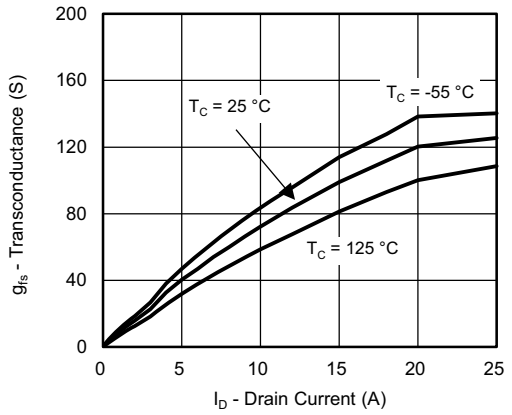
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



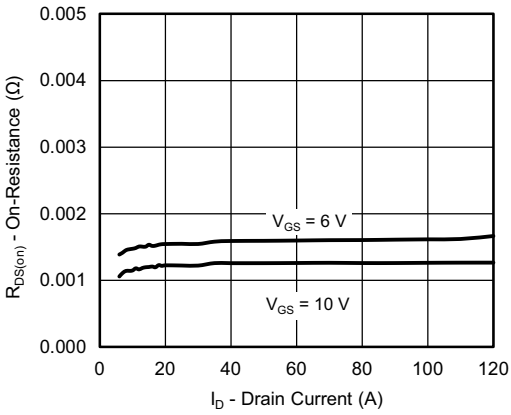
Output Characteristics



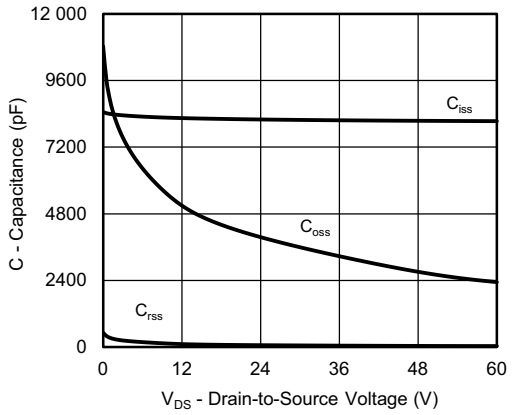
Transfer Characteristics



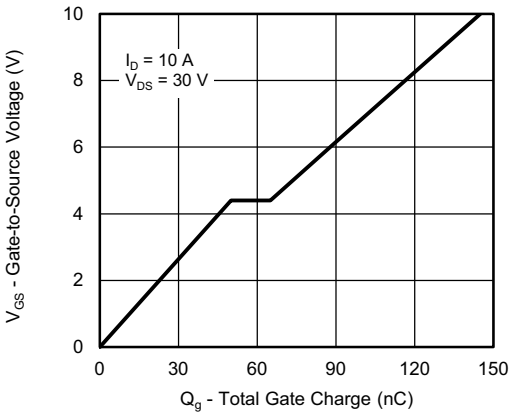
Transconductance



On-Resistance vs. Drain Current

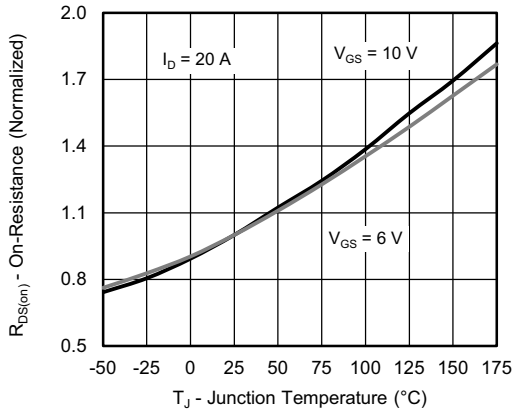


Capacitance

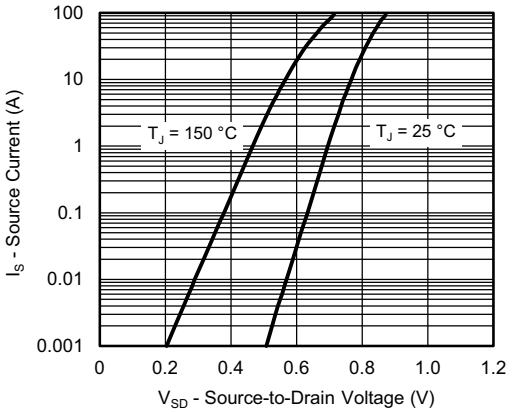


Gate Charge

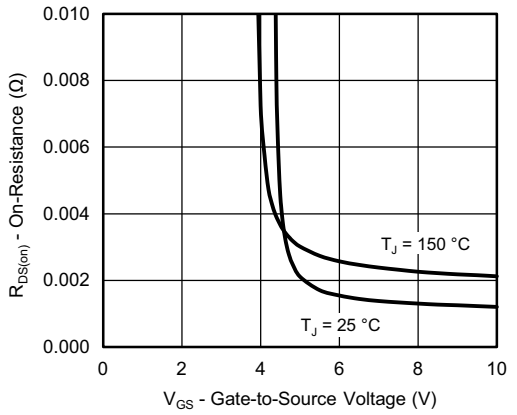
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



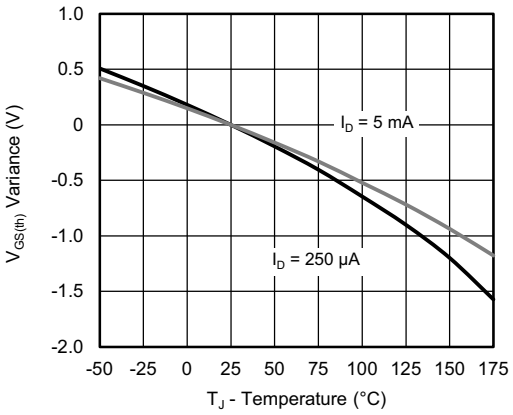
On-Resistance vs. Junction Temperature



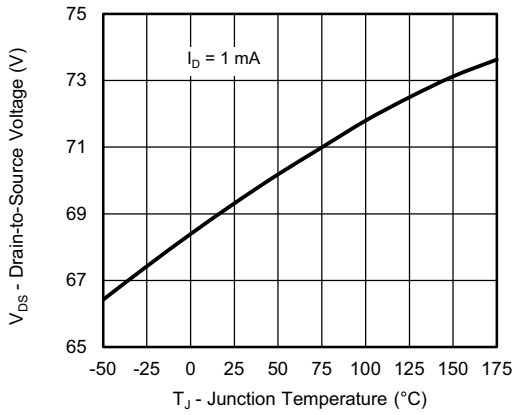
Source Drain Diode Forward Voltage



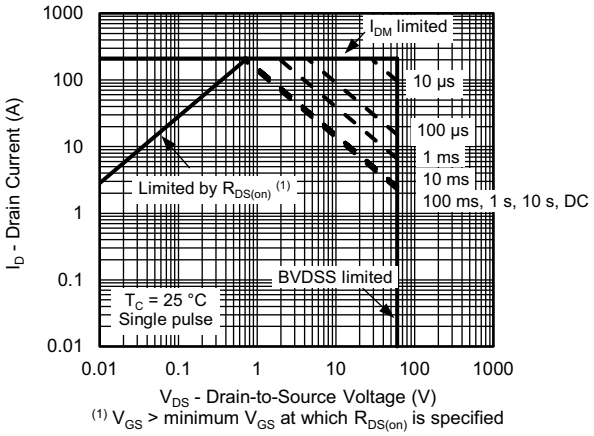
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

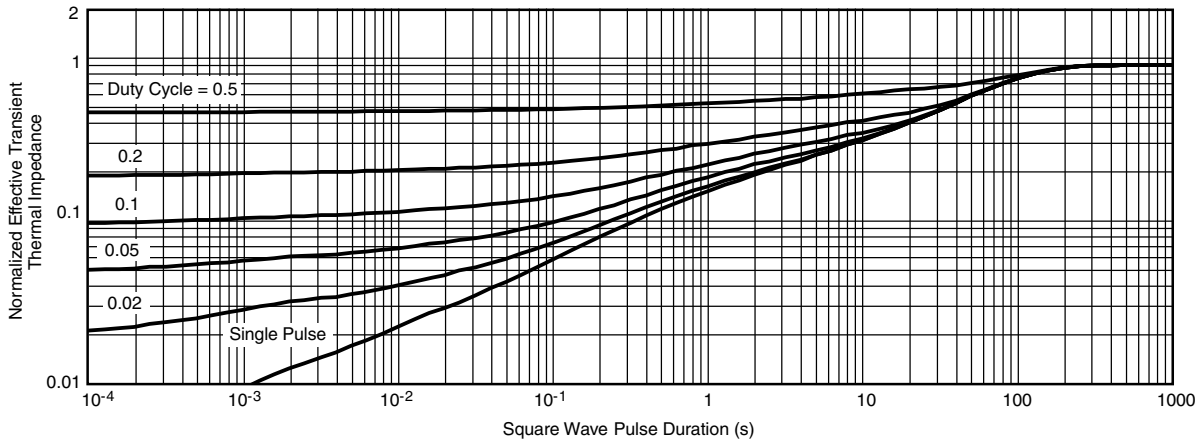


Drain Source Breakdown vs. Junction Temperature

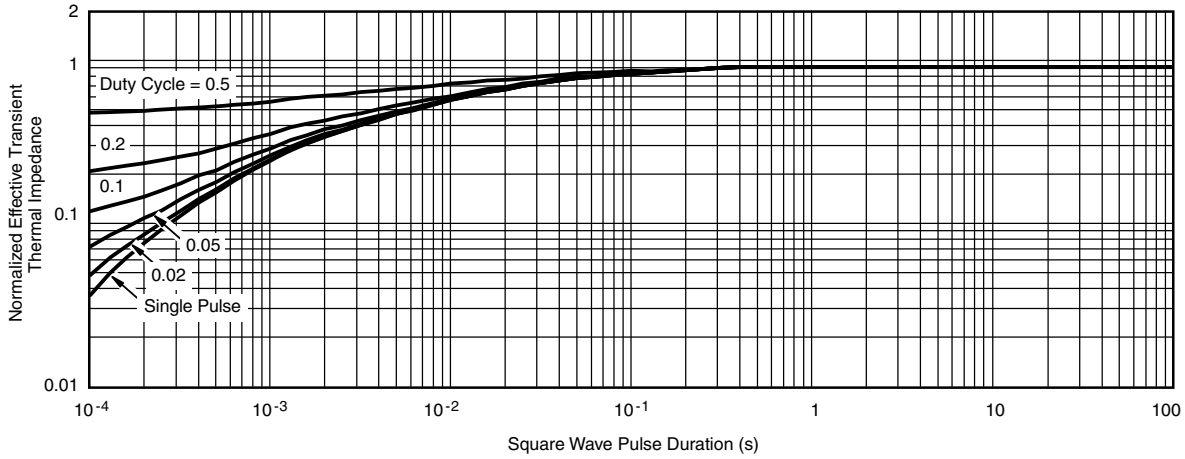


Safe Operating Area

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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